



**THE DATASHEET OF  
1N4531,113**



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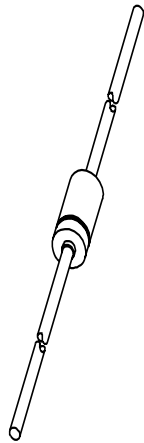
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Kind regards,

Team Nexperia

# DATA SHEET



## **1N4531; 1N4532** High-speed diodes

Product data sheet  
Supersedes data of April 1996

1996 Sep 03

# High-speed diodes

# 1N4531; 1N4532

## FEATURES

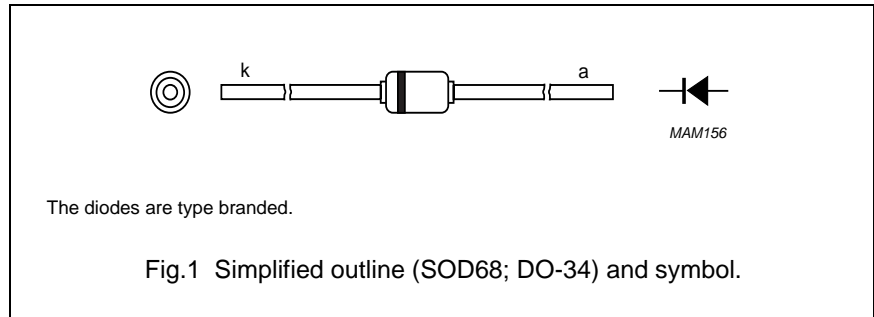
- Hermetically sealed leaded glass SOD68 (DO-34) package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 450 mA.

## APPLICATIONS

- High-speed switching
- Protection diodes in reed relays.

## DESCRIPTION

The 1N4531, 1N4532 are high-speed switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD68 (DO-34) packages.



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL    | PARAMETER                           | CONDITIONS   | MIN. | MAX.          | UNIT        |
|-----------|-------------------------------------|--|------|---------------|-------------|
| $V_{RRM}$ | repetitive peak reverse voltage     |  | –    | 75            | V           |
| $V_R$     | continuous reverse voltage          |  | –    | 75            | V           |
| $I_F$     | continuous forward current          | see Fig.2  | –    | 200           | mA          |
| $I_{FRM}$ | repetitive peak forward current     |  | –    | 450           | mA          |
| $I_{FSM}$ | non-repetitive peak forward current | square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4<br>$t = 1\ \mu\text{s}$<br>$t = 1\ \text{ms}$<br>$t = 1\ \text{s}$ | –    | 4<br>1<br>0.5 | A<br>A<br>A |
| $P_{tot}$ | total power dissipation             | $T_{amb} = 25\text{ °C}$   | –    | 500           | mW          |
| $T_{stg}$ | storage temperature                 |  | –65  | +200          | °C          |
| $T_j$     | junction temperature                |  | –    | 200           | °C          |

## High-speed diodes

## 1N4531; 1N4532

**ELECTRICAL CHARACTERISTICS**T<sub>j</sub> = 25 °C; unless otherwise specified.

| SYMBOL          | PARAMETER                | CONDITIONS  | MIN. | MAX. | UNIT |
|-----------------|--------------------------|---|------|------|------|
| V <sub>F</sub>  | forward voltage          | I <sub>F</sub> = 10 mA; see Fig.3   | –    | 1000 | mV   |
| I <sub>R</sub>  | reverse current          | see Fig.5   |      |      |      |
|                 | IN4531                   | V <sub>R</sub> = 20 V   | –    | 25   | nA   |
|                 |                          | V <sub>R</sub> = 20 V; T <sub>j</sub> = 150 °C  | –    | 50   | μA   |
|                 | IN4532                   | V <sub>R</sub> = 50 V   | –    | 100  | nA   |
|                 |                          | V <sub>R</sub> = 50 V; T <sub>j</sub> = 150 °C  | –    | 100  | μA   |
| C <sub>d</sub>  | diode capacitance        | f = 1 MHz; V <sub>R</sub> = 0; see Fig.6  |      |      |      |
|                 | IN4531                   |   | –    | 4    | pF   |
|                 | IN4532                   |   | –    | 2    | pF   |
| t <sub>rr</sub> | reverse recovery time    | when switched from I <sub>F</sub> = 10 mA to I <sub>R</sub> = 60 mA; R <sub>L</sub> = 100 Ω; measured at I <sub>R</sub> = 1 mA; see Fig.7 |      |      |      |
|                 | IN4531                   |   | –    | 4    | ns   |
|                 | IN4532                   |   | –    | 2    | ns   |
|                 | reverse recovery time    | when switched from I <sub>F</sub> = 10 mA to I <sub>R</sub> = 10 mA; R <sub>L</sub> = 100 Ω; measured at I <sub>R</sub> = 1 mA; see Fig.7 |      |      |      |
|                 | IN4532                   |   | –    | 4    | ns   |
| V <sub>fr</sub> | forward recovery voltage | when switched from I <sub>F</sub> = 100 mA; t <sub>r</sub> ≤ 30 ns; see Fig.8   | –    | 3    | V    |

**THERMAL CHARACTERISTICS**

| SYMBOL               | PARAMETER                                     | CONDITIONS               | VALUE | UNIT |
|----------------------|---|--------------------------|-------|------|
| R <sub>th j-tp</sub> | thermal resistance from junction to tie-point | lead length 5 mm         | 120   | K/W  |
| R <sub>th j-a</sub>  | thermal resistance from junction to ambient   | lead length 5 mm; note 1 | 350   | K/W  |

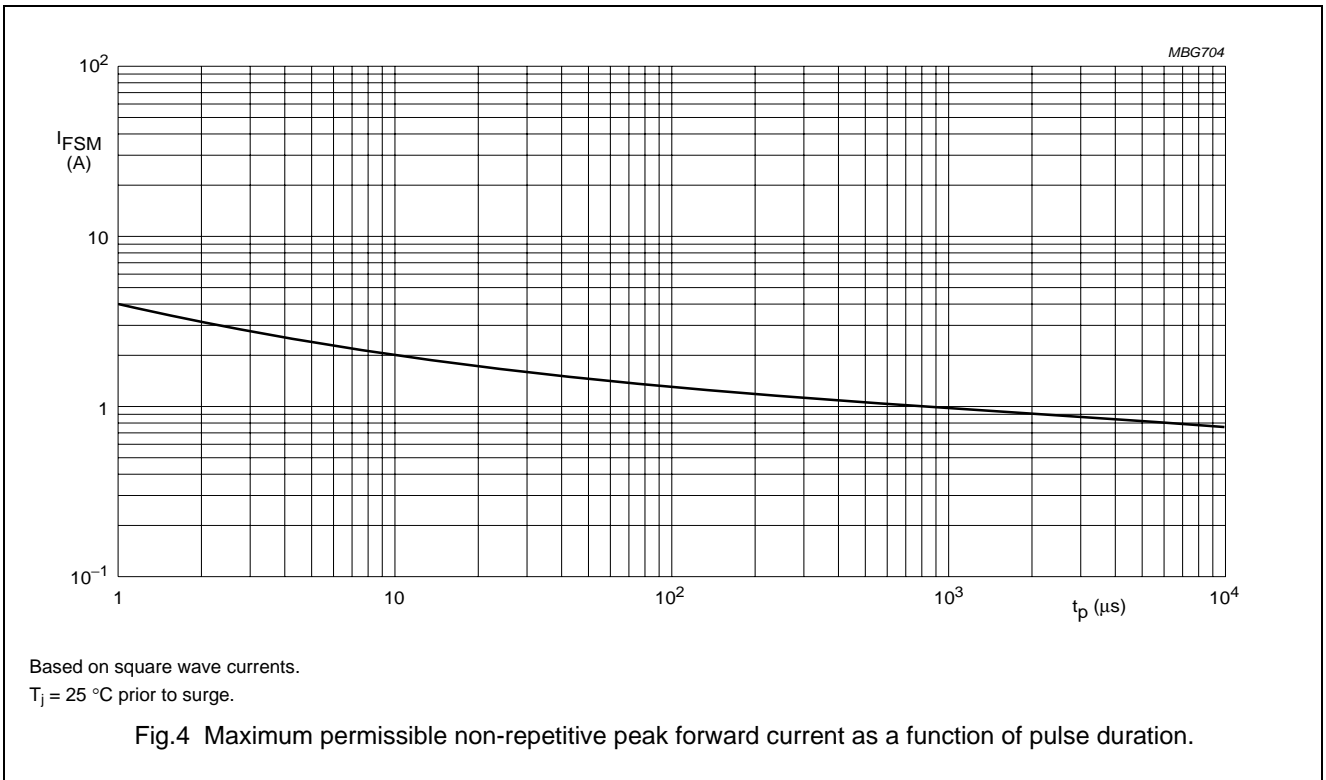
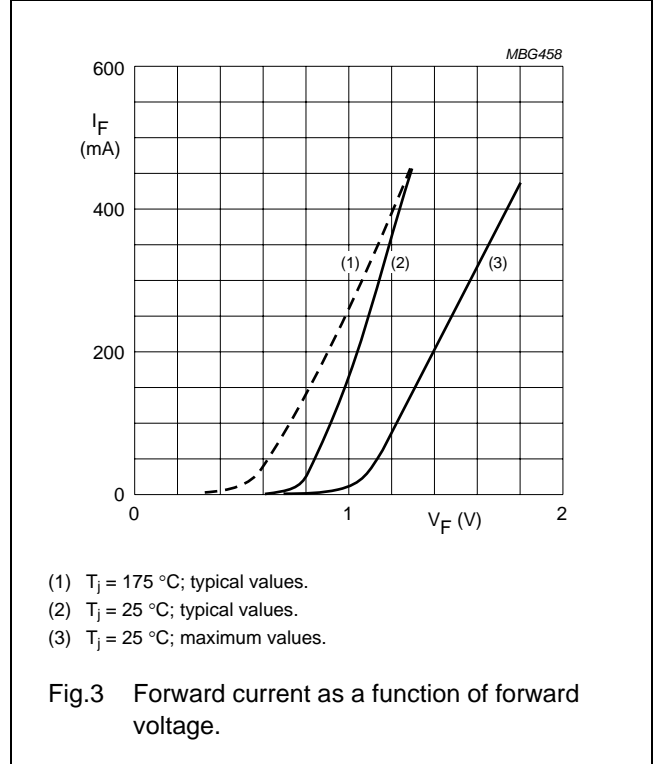
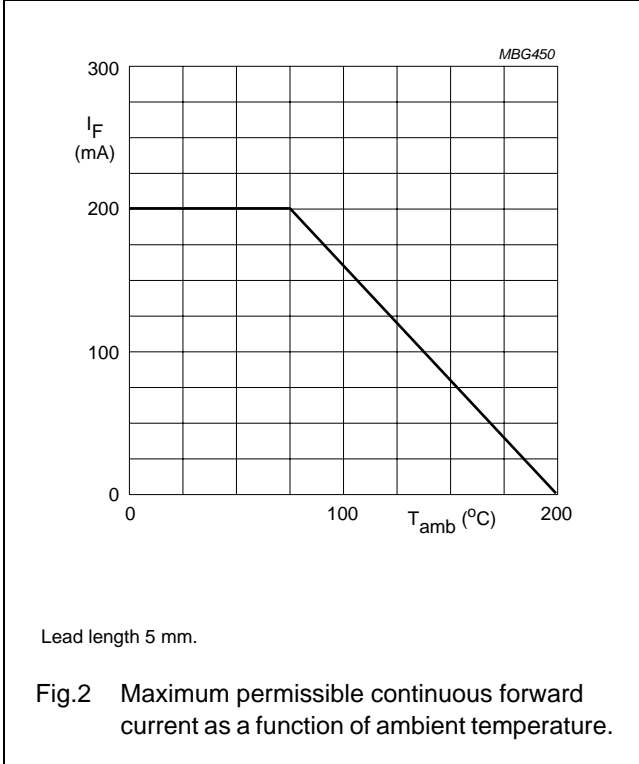
**Note**

1. Device mounted on a printed circuit-board without metallization pad.

High-speed diodes

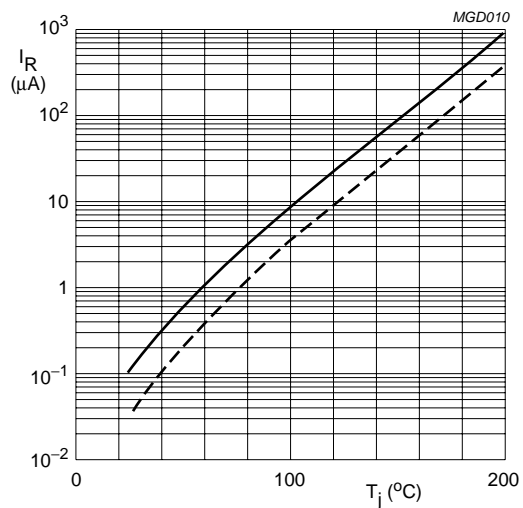
1N4531; 1N4532

GRAPHICAL DATA



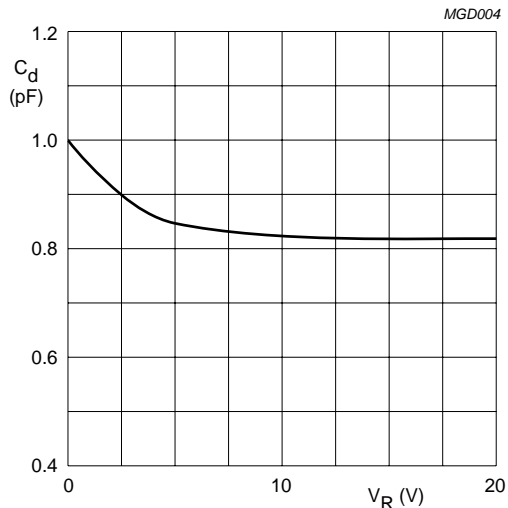
High-speed diodes

1N4531; 1N4532



$V_R = 50\text{ V}$   
 Solid line; maximum values.  
 Dotted line; typical values.

Fig.5 Reverse current as a function of junction temperature.

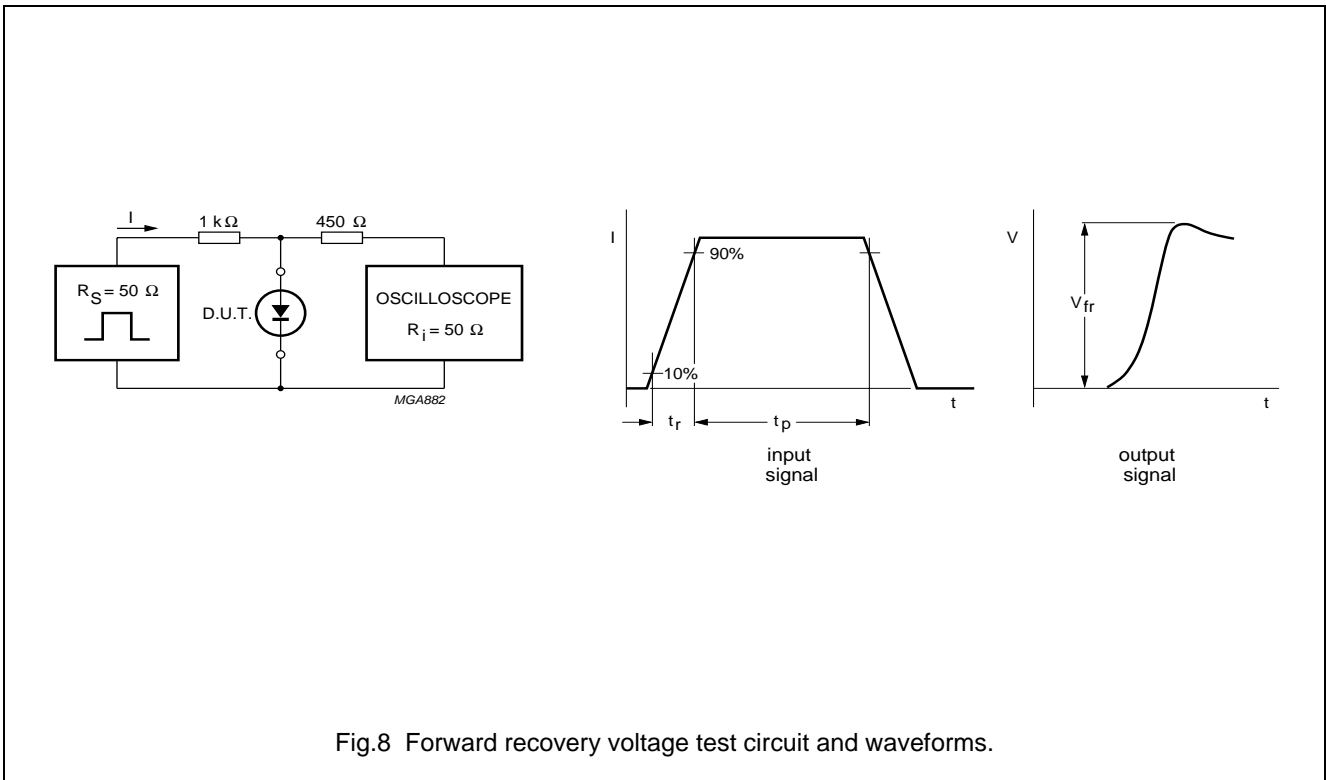
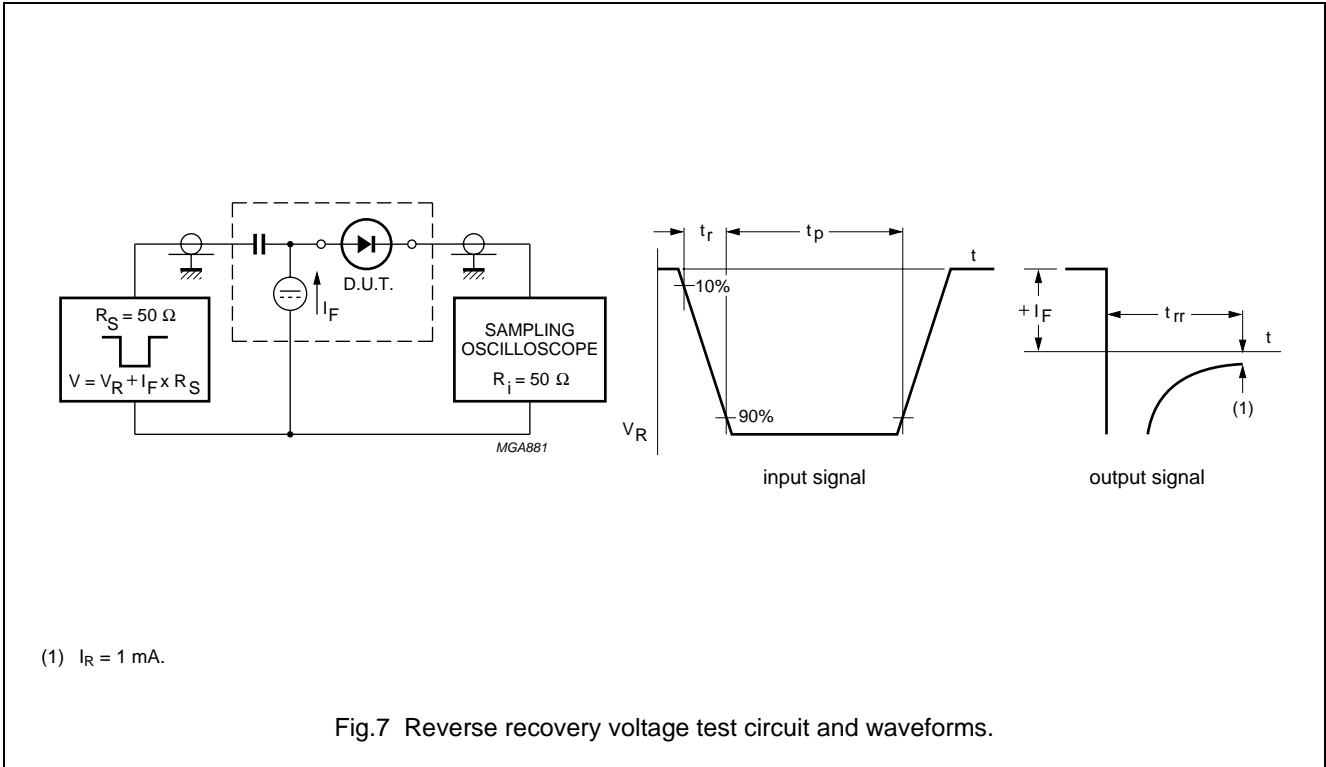


$f = 1\text{ MHz}; T_j = 25\text{ °C}.$

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed diodes

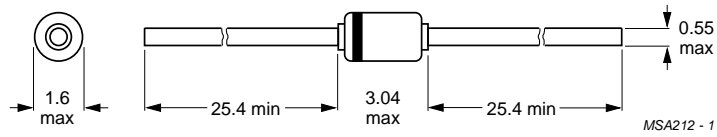
1N4531; 1N4532



High-speed diodes

1N4531; 1N4532

PACKAGE OUTLINE



Dimensions in mm.

Fig.9 SOD68 (DO-34).

## High-speed diodes

1N4531; 1N4532

## DATA SHEET STATUS

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION  |
|--------------------------------|-------------------------------|---|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

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# ***NXP Semiconductors***

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## **Contact information**

For additional information please visit: **<http://www.nxp.com>**

For sales offices addresses send e-mail to: **[salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)**

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